2SK2660(Tentative)

Silicon N-Channel Power F-MOS

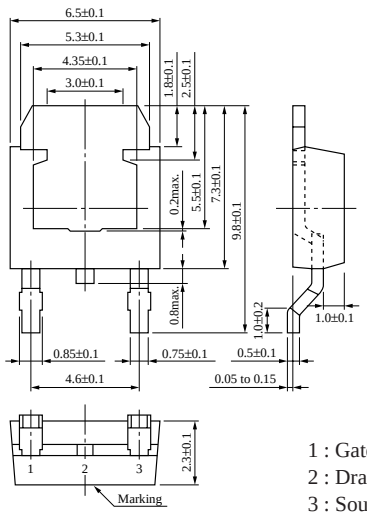
■ Features

- High-speed switching
- High drain-source voltage (V_{DSS})

■ Applications

- High-speed switching

Unit : mm



1 : Gate
2 : Drain
3 : Source
EIAJ : SC-63
U Type Package

■ Absolute Maximum Ratings (Tc = 25˚C)

Parameter		Symbol	Rating	Unit
Drain-Source breakdown voltage		V_{DSS}	200	V
Gate-Source voltage		V_{GSS}	±30	V
Drain current	DC	I_D	±4	A
	Pulse	I_{DP}	±8	A
Allowable power dissipation	T_C= 25˚C	P_D	10	W
	Ta= 25˚C		0.75	
Channel temperature		T_{ch}	150	˚C
Storage temperature		T_{stg}	–55 to +150	˚C

■ Electrical Characteristics (Tc = 25˚C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I_{DSS}	V_{DS}=160V, V_{GS}= 0			0.1	m A
Gate-Source leakage current	I_{GSS}	V_{GS}=±30V, V_{DS}= 0			±1	µ A
Drain-Source breakdown voltage	V_{DSS}	I_D=1mA, V_{GS}= 0	200			V
Gate threshold voltage	V_{th}	V_{DS}= 25V, I_D=1mA	1		5	V
Drain-Source ON-resistance	$R_{DS(on)}$	V_{GS}=10V, I_D= 2A		0.8	1.1	Ω
Forward transadmittance	$\|Y_{fs}\|$	V_{DS}= 25V, I_D= 2A, f=1MHz	0.8	1.6		S
Input capacitance	C_{iss}	V_{DS}= 20V, V_{GS}= 0, f=1MHz		300		pF
Output capacitance	C_{oss}			60		pF
Feedback capacitance	C_{rss}			10		pF
Turn-on time	t_{on}	V_{GS}=10V, I_D= 2A V_{DD}=100V, R_L= 200Ω		30		ns
Fall time	t_f			50		ns
Turn-off time (delay time)	$t_{d(off)}$			20		ns